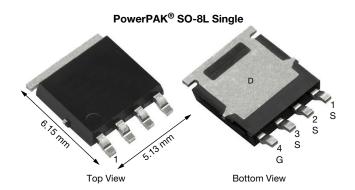


www.vishay.com

Vishay Siliconix

# Automotive N-Channel 200 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY				
V <sub>DS</sub> (V)	200			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0500			
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = 7.5 \text{ V}$	0.0520			
I <sub>D</sub> (A)	22.5			
Configuration	Single			

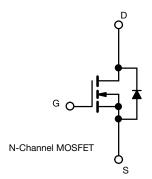
#### **FEATURES**

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R<sub>q</sub> and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ROHS COMPLIANT HALOGEN FREE



ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and halogen-free	SQJA20EP (for detailed order number please see <a href="https://www.vishay.com/doc?79771">www.vishay.com/doc?79771</a> )

ABSOLUTE MAXIMUM RATINGS (To	<sub>C</sub> = 25 °C, unles	ss otherwise noted)			
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage Gate-source voltage		$V_{DS}$	200	V	
		$V_{GS}$	± 20	V	
Continuous drain current	T <sub>C</sub> = 25 °C	I-	22.5		
Continuous drain current	T <sub>C</sub> = 125 °C	I <sub>D</sub>	13		
Continuous source current (diode conduction)		I <sub>S</sub>	60	Α	
Pulsed drain current <sup>a</sup>		I <sub>DM</sub>	82		
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	18		
Single pulse avalanche energy	L = 0.1 IIIII	E <sub>AS</sub>	16	mJ	
Maximum power dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	P <sub>D</sub>	68	W	
iviaximum power dissipation -	T <sub>C</sub> = 125 °C	ГD	22	VV	
Operating junction and storage temperature range	Э	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	
Soldering recommendations (peak temperature) c,	, d		260	C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount b	$R_{thJA}$	68	°C/W
Junction-to-case (drain)		$R_{thJC}$	2.2	C/VV

#### Notes

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %
- b. When mounted on 1" square PCB (FR4 material)
- c. See solder profile (<a href="https://www.vishay.com/doc?73257">www.vishay.com/doc?73257</a>). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- d. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components



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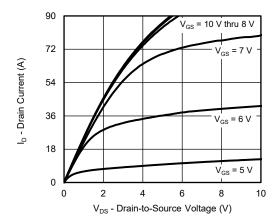
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub>	= 0, I <sub>D</sub> = 250 μA	200	-	-	V
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	= V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2.5	3.0	3.5	V
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	0 V, V <sub>GS</sub> = ± 20 V	-	-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = 200 V	-	-	1	
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 200 V, T <sub>J</sub> = 125 °C	-	-	50	μΑ
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 200 V, T <sub>J</sub> = 175 °C	-	-	200	1
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	V <sub>DS</sub> ≥ 5 V	10	-	-	Α
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 10 A	-	0.0410	0.0500	
Desire and the second second	5	V <sub>GS</sub> = 7.5 V	I <sub>D</sub> = 8 A	-	0.0426	0.0520	
Drain-source on-state resistance a	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 10 A, T <sub>J</sub> = 125 °C	200 2.5 °C - 10	-	0.1020	Ω
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 10 A, T <sub>J</sub> = 175 °C	-	-	0.1350	
Forward transconductance b	9fs	V <sub>DS</sub>	= 15 V, I <sub>D</sub> = 10 A	-	19	-	S
Dynamic <sup>b</sup>							•
Input capacitance	C <sub>iss</sub>			-	955	1300	
Output capacitance	Coss	$V_{GS} = 0 V$	V <sub>DS</sub> = 25 V, f = 1 MHz	-	456	650	рF
Reverse transfer capacitance	C <sub>rss</sub>			-	38	55	
Total note shown C	0	V <sub>GS</sub> = 10 V	$V_{DS} = 100 \text{ V}, I_D = 5 \text{ A}$	-	17.6	27	
Total gate charge <sup>c</sup>	$Q_g$			-	14.1	22	0
Gate-source charge c	Q <sub>gs</sub>	$V_{GS} = 7.5 \text{ V}$	$V_{DS} = 100 \text{ V}, I_{D} = 5 \text{ A}$	-	4.1	-	nC
Gate-drain charge c	Q <sub>gd</sub>			-	5.3	-	
Gate resistance	$R_g$		f = 1 MHz	0.55	1.18	1.80	Ω
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>			-	14	25	
Rise time <sup>c</sup>	t <sub>r</sub>	V <sub>DD</sub> =	$= 100 \text{ V}, R_L = 20 \Omega$	-	4	10	
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 5 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		-	27	45	ns
Fall time <sup>c</sup>	t <sub>f</sub>			-	12	20	
Source-Drain Diode Ratings and Charac	teristics <sup>b</sup>						
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	82	Α
Forward voltage	V <sub>SD</sub>	I <sub>F</sub> :	= 10 A, V <sub>GS</sub> = 0	-	0.81	1.2	V
Body diode reverse recovery time	t <sub>rr</sub>			-	88	180	ns
Body diode reverse recovery charge	Q <sub>rr</sub>	] , ,	A di/dt = 100 A/ua	-	301	600	nC
Reverse recovery fall time	t <sub>a</sub>	] IF = 5	A, di/dt = 100 A/μs	-	69	-	
Reverse recovery rise time	t <sub>b</sub>	1		-	19	-	ns
Body diode peak reverse recovery current	I <sub>RM(REC)</sub>			-	-6.7	-	Α

#### Notes

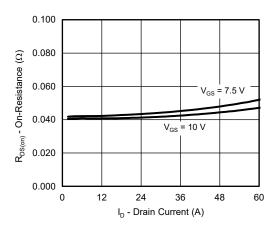
- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

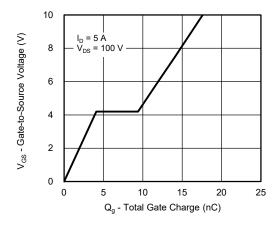




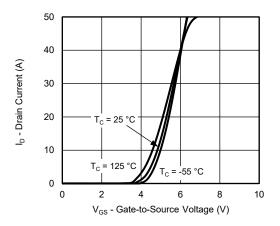
### **Output Characteristics**



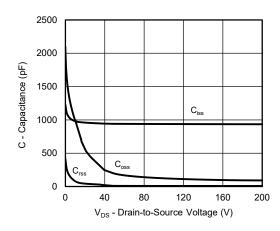
On-Resistance vs. Drain Current



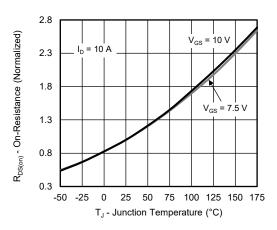
**Gate Charge** 



**Transfer Characteristics** 



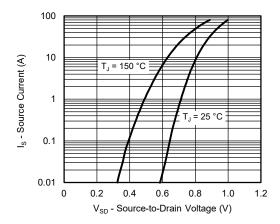
Capacitance



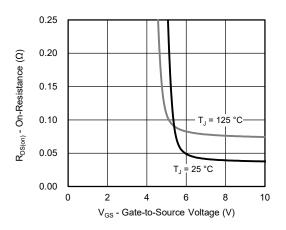
On-Resistance vs. Junction Temperature

For technical questions, contact: automoste

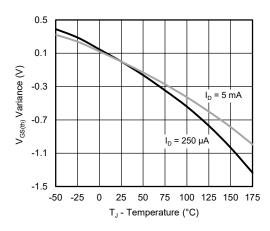




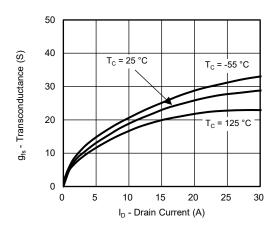
**Source Drain Diode Forward Voltage** 



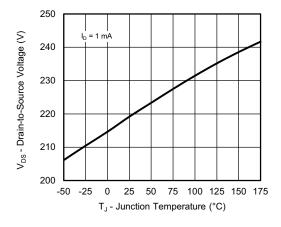
On-Resistance vs. Gate-to Source Voltage



**Threshold Voltage** 



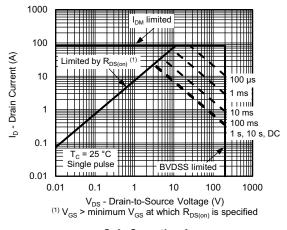
Transconductance



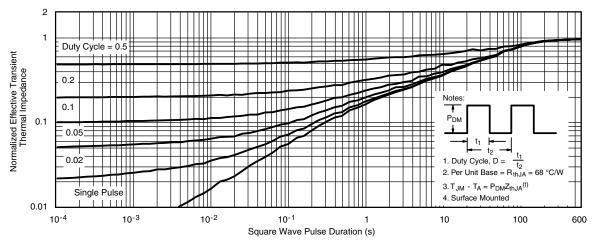
**Drain Source Breakdown vs. Junction Temperature** 

For technical questions, contact: automostech



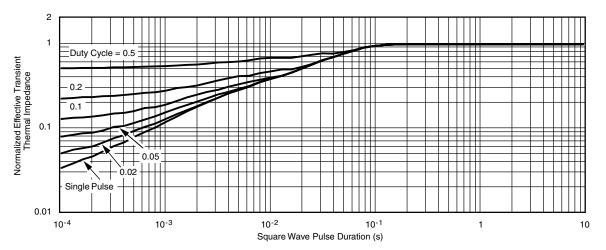


Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient





Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?75420.



# PowerPAK® SO-8L Case Outline 2



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DIM		MILLIMETERS		INCHES			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
Α	1.00	1.07	1.14	0.039	0.042	0.045	
A1	0.00	-	0.127	0.00	-	0.005	
b	0.33	0.41	0.48	0.013	0.016	0.019	
b1	0.44	0.51	0.58	0.017	0.020	0.023	
b2	4.80	4.90	5.00	0.189	0.193	0.197	
b3		0.094			0.004		
b4		0.47			0.019		
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	5.00	5.13	5.25	0.197	0.202	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D3	1.63	1.73	1.83	0.064	0.068	0.072	
е		1.27 BSC		0.050 BSC			
Е	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2	2.75	2.85	2.95	0.108	0.112	0.116	
E3	6.05	6.22	6.40	0.238	0.245	0.252	
F	-	-	0.15	-	-	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
K		0.51		0.020			
W	0.23		0.009				
W1		0.41		0.016			
W2	2.82		0.111				
W3		2.96		0.117			
θ	0°	-	10°	0°	-	10°	

DWG: 6044

#### Note

• Millimeters will govern



### RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)



## **Legal Disclaimer Notice**

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